

FIG 1 prior art

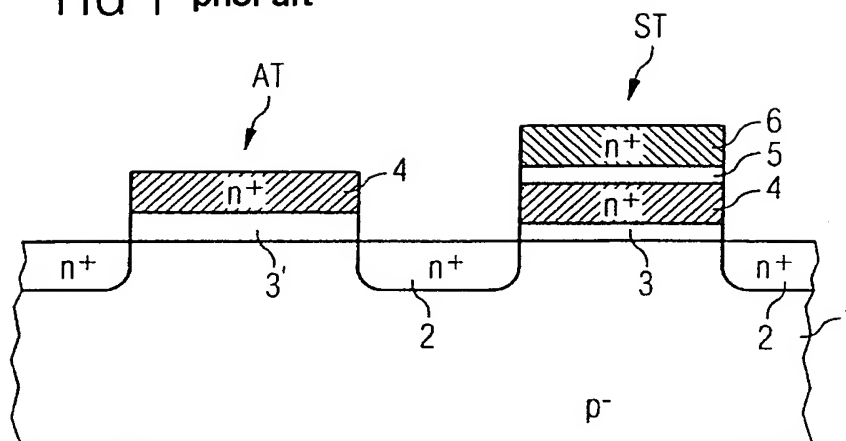


FIG 2

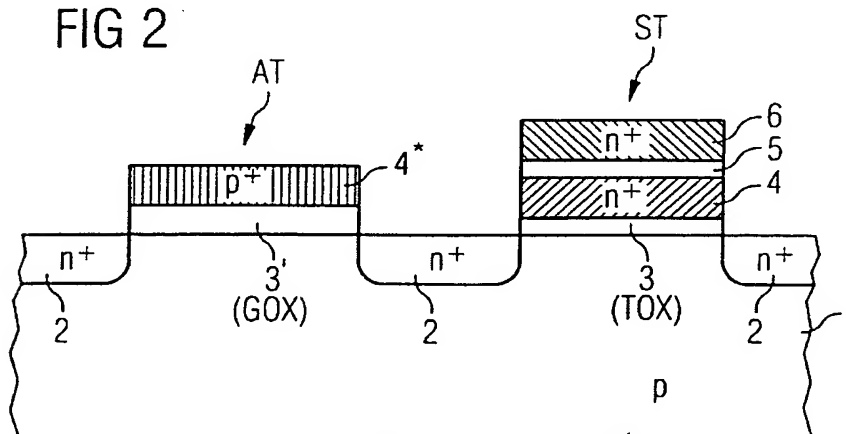


FIG 3A

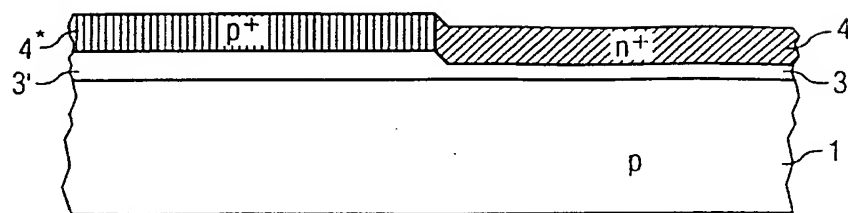


FIG 3B

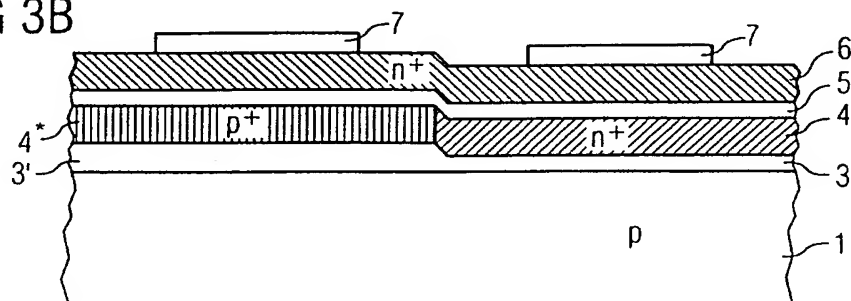


FIG 3C

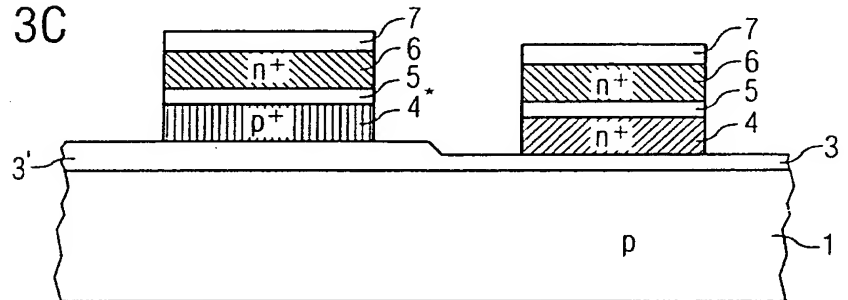


FIG 3D

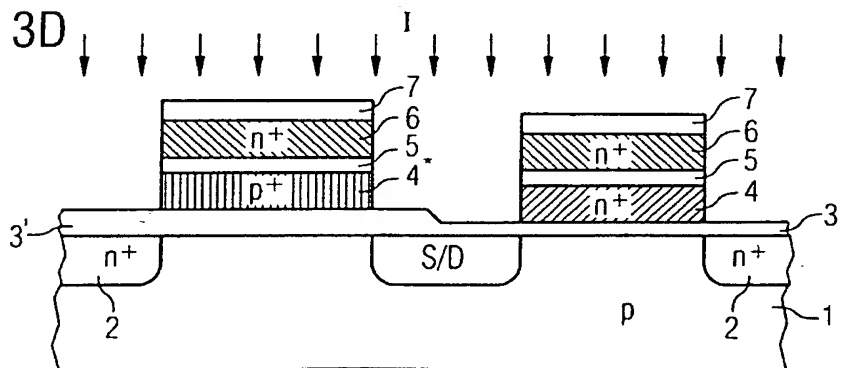


FIG 4A

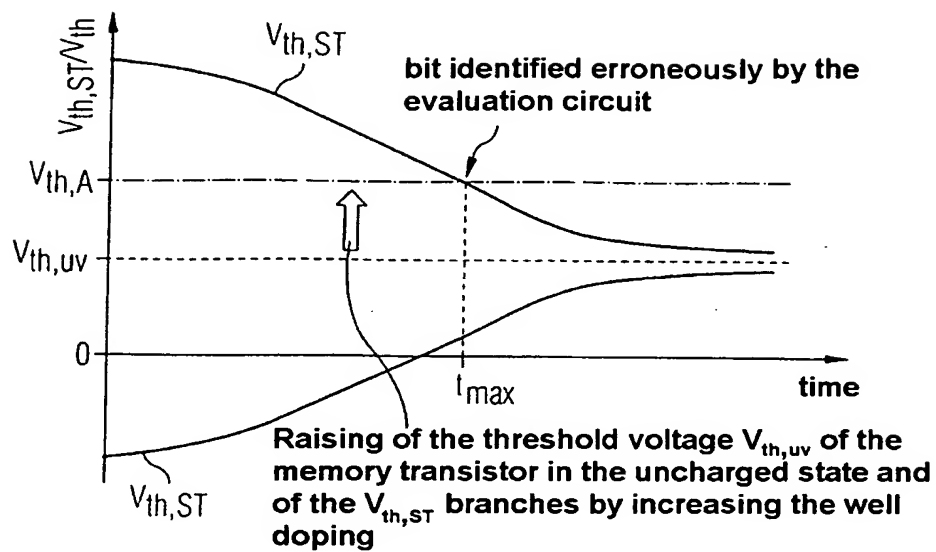


FIG 4B

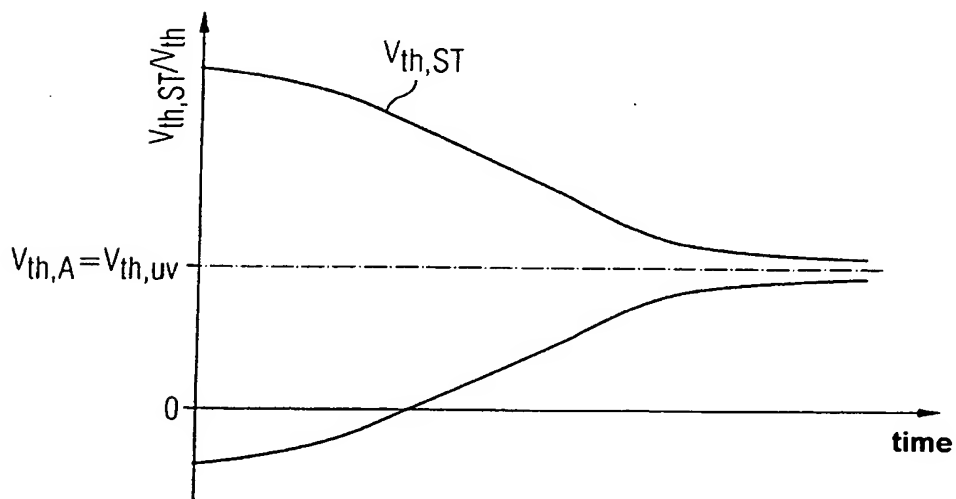


FIG 5A

Difference in the threshold voltage results on account of coupling effects of the different insulation layers (G_{ox} , T_{ox})

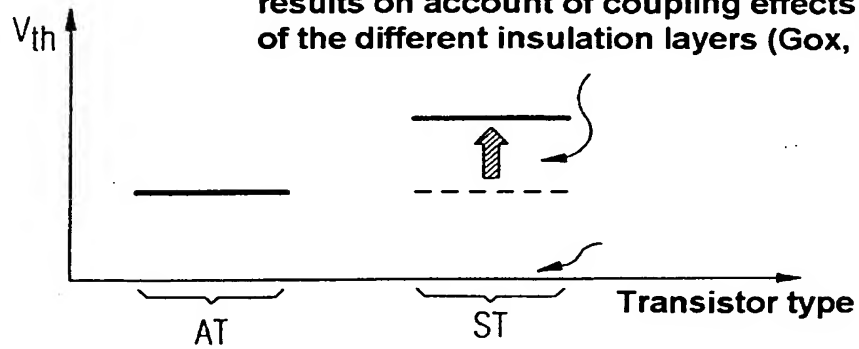


FIG 5B

Raising of the threshold voltage on account of increased well doping

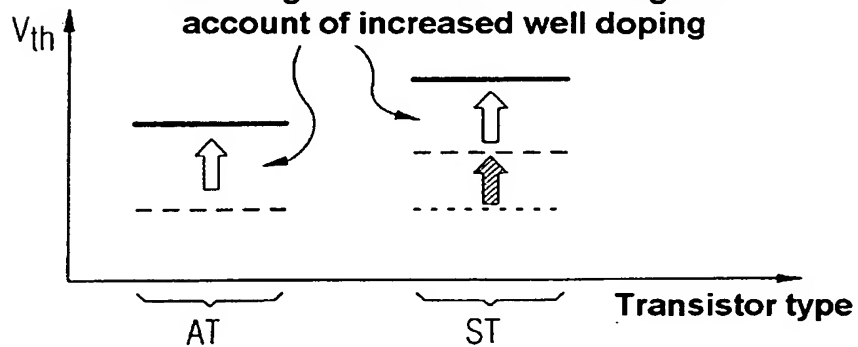


FIG 5C

Change in the work function of the control layer in the selection transistor (e.g. by means of p-type doping)

